

a buried semiconductor layer of a second conduction type formed in a first region of the semiconductor substrate, spaced from a surface of the semiconductor substrate;

a semiconductor region of the second conduction type extending from the surface of the semiconductor substrate to a peripheral portion of the buried semiconductor layer and;

A1
Cont a semiconductor region of the first conduction type formed in the semiconductor substrate surrounded by the buried semiconductor layer and the semiconductor region of the second conduction type,

wherein a concentration of an impurity of the semiconductor region of the first conduction type is almost equal to a concentration of an impurity of the semiconductor substrate.

REMARKS

The Office Action mailed January 24, 2000, having been duly extended from April 24, 2000 until June 26, 2000 by the attached Petition for Extension of Time, has been received and carefully noted. The above amendments and the following remarks are submitted as a full and complete response thereto. Claim 1 has been amended to more particularly point out and distinctly claim the subject matter to which it is directed. Claims 1-7 are respectfully submitted for consideration.

The Title of the Invention was objected to as not being not being descriptive. Applicants have provided a new title which is clearly indicative of the claimed subject matter.

Claims 1-3, 5, and 6 were rejected under 35 USC §102(a) as being anticipated by